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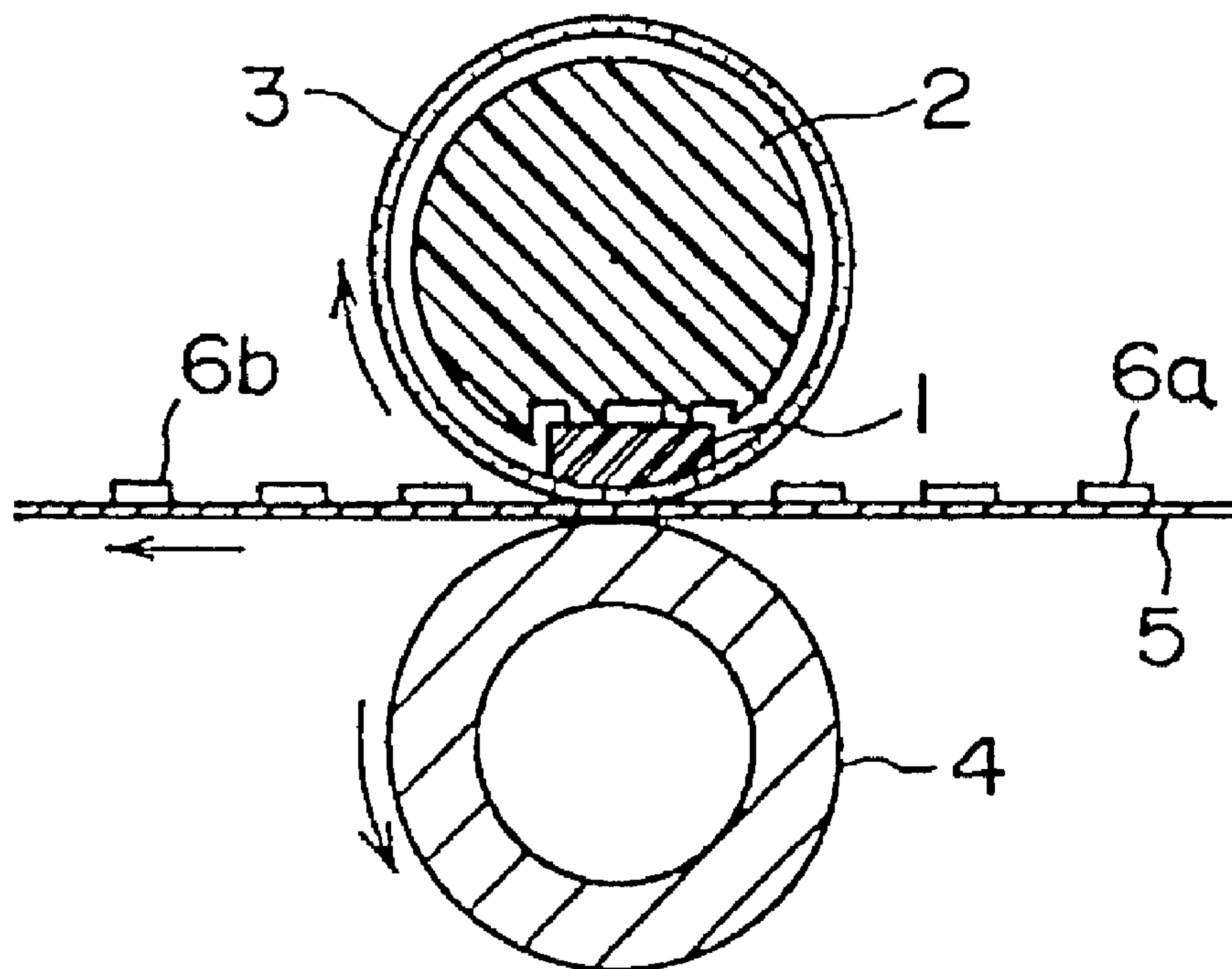
(72) Inventeurs/Inventors:
NATSUHARA, MASUHIRO, JP;
NAKATA, HIROHIKO, JP;
TANAKA, MOTOYUKI, JP;
YUSHIO, YASUHISA, JP

(73) Propriétaire/Owner:
SUMITOMO ELECTRIC INDUSTRIES, LTD., JP

(74) Agent: G. RONALD BELL & ASSOCIATES

(54) Titre : METHODE DE POLISSAGE D'UN SUBSTRAT EN CERAMIQUE

(54) Title: CERAMIC SUBSTRATE POLISHING METHOD



(57) Abrégé/Abstract:

A ductile rotating body containing abrasive grains is used, and the surface of a ceramic substrate is polished by the circumferential portion of rotating body. At this time, angle θ formed between the polishing direction D_0 of ceramic substrate and the rotating direction D_1 of rotating body is set in the range from 10° to 80° for polishing. Alternatively, the polishing process is divided into at least two steps, and the average grain size of abrasive grains is reduced stepwise for polishing. According to this method, the surface of a large-area and thin ceramic substrate can be polished without damages, and a ceramic surface having a smooth polished surface can be provided. This method is particularly suitable for polishing a ceramic substrate having a thickness of at most 2.0mm, and the resulting polished ceramic substrate is suitable for a substrate for a ceramic heater in a thermal fixation device for toner image.



ABSTRACT OF THE DISCLOSURE

A ductile rotating body containing abrasive grains is used, and the surface of a ceramic substrate is polished by the circumferential portion of rotating body. At this time, angle θ formed between the polishing
5 direction D_0 of ceramic substrate and the rotating direction D_1 of rotating body is set in the range from 10° to 80° for polishing. Alternatively, the polishing process is divided into at least two steps, and the average grain size of abrasive grains is reduced stepwise for polishing. According to this method, the surface of a large-area and thin ceramic substrate can be
10 polished without damages, and a ceramic surface having a smooth polished surface can be provided. This method is particularly suitable for polishing a ceramic substrate having a thickness of at most 2.0mm, and the resulting polished ceramic substrate is suitable for a substrate for a ceramic heater in a thermal fixation device for toner image.

TITLE OF THE INVENTION

Ceramic Substrate Polishing Method

BACKGROUND OF THE INVENTION

Field of the Invention

5 The present invention relates to ceramic substrates having a polished surface with high surface smoothness and methods of polishing such ceramic substrates, and more particularly, to a ceramic substrate for use in a thermal fixation device for toner image such as a copying machine and a printer and a method of polishing such a ceramic substrate.

10 Description of the Background Art

 Conventionally, when a ceramic material is used for various purposes, in general, the surface of the ceramic material should be polished or ground into smoothness. There have been various proposed methods of smoothing a ceramic surface depending upon the shape, use, required
15 smoothness and the like of the ceramic material.

 One typical method of polishing a ceramic material is barrel-polishing, according to which a ceramic material and an abrasive are put together into a container to polish the ceramic material by rotation or vibration, and Japanese Patent Laying-Open No. 58-192745 for example
20 discloses a method of polishing a ceramic element by a vibrating barrel using a pier-shaped abrasive.

 Other methods of treating a ceramic surface include lapping, honing, and grinding. These methods employ hone or abrasive grains to pressurize the ceramic material to be treated and the surface is ground.

25 The conventional, typical methods of polishing or grinding described above are suitable for treating relatively small and thick ceramic elements, but are not appropriate for smoothing the surface of a ceramic substrate having a large area and a relatively small thickness such as a substrate for a ceramic heater in a thermal fixation device for toner image.

30 In barrel-polishing, for example, a thin ceramic substrate is sometimes destroyed by a grinder during rotation or vibration. In lapping, honing, and grinding, a ceramic substrate is prone to cracking, because a prescribed pressure is applied between abrasive grains or a grinder used

and the ceramic material.

The lapping, honing, grinding or the like requests that the untreated surface must be ground as much as 0.1 to 0.2 mm in order to eliminate variations in the surface smoothness by the working. Therefore, a ceramic substrate having a thickness larger than a finished product by the margin for working should be prepared, which increases the material cost.

SUMMARY OF THE INVENTION

The present invention is directed to a solution to the problem, and it is an object of the present invention to provide a method of polishing the surface of a ceramic substrate having a large area and a relatively small thickness into smoothness without damaging the surface.

In order to achieve the above-described object, according to one aspect of the present invention, there is provided a method of polishing a ceramic substrate, wherein a ductile rotating body containing abrasive grains is used, and one surface of the ceramic substrate is polished while the ceramic substrate is moved in one direction, wherein a thickness of the ceramic substrate is, at most, 2.0 mm, and the direction orthogonal to the rotating axis of the rotating body is inclined at an angle in the range of from 10° to 80° relative to the direction of polishing the ceramic substrate.

If the angle is smaller than 10° or larger than 80°, a line is impressed on the ceramic substrate by the abrasive grains, and the surface roughness is relatively increased.

The polishing process may be divided into two or more steps and the average grain size of abrasive grains contained in the rotating body may be reduced stepwise.

The present invention also provides a method of polishing a ceramic substrate, which comprises providing and rotating a first ductile body containing first abrasive grains; polishing a first surface of the ceramic substrate using the rotating first ductile body, by contacting a circumferential portion of the rotating first ductile body onto the first surface of the ceramic substrate; and linearly moving one of the first ductile body and the ceramic substrate or both thereof relative to each other along a linear polishing direction while carrying out the polishing, wherein the linear polishing direction is oriented at an angle in a range from 10° to 80° relative to a rotation direction that is orthogonal to a rotation axis about which the first ductile body is rotating.

According to another aspect of the present invention, which is claimed in Divisional Application Serial No. 2,400,852, there is provided a ceramic substrate resulting from the polishing as described above which has at least one surface polished, which surface is formed by a substantially flat portion and a recessed portion remaining in the flat portion.

Such a ceramic substrate is suitable for a ceramic substrate having a large area and a relatively small thickness such as a substrate for a ceramic heater used in a thermal fixation device for toner image. The flat portion herein includes microscopically small irregularities.

5 The foregoing and other objects, features, aspects and advantages of the present invention will become more apparent from the following detailed description of the present invention when taken in conjunction with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

10 Fig. 1 is a schematic conceptual view of a cross section of a ceramic substrate before polished for illustrating the surface state;

Fig. 2 is a schematic conceptual view of a cross section of a ceramic substrate after polished by a polishing method according to the present invention for illustrating the surface state;

15 Fig. 3 is a schematic plan view for use in illustration of the relation of the advancing direction of a ceramic substrate and the rotating direction of a rotating body when the ceramic substrate is polished using the rotating body by a polishing method according to the present invention;

20 Fig. 4 is a schematic cross sectional view of a thermal fixation device for toner image using a ceramic heater;

Fig. 5 is a schematic plan view of a ceramic heater used in a thermal fixation device for toner image;

Fig. 6 is a graph of the roughness curve of the surface of an aluminum nitride sintered body before polished;

25 Fig. 7 is a graph of the roughness curve of the surface of the aluminum nitride sintered body shown in Fig. 6 after polished by a method according to the present invention;

Fig. 8 is a graph of the roughness curve of the surface of the aluminum nitride sintered body shown in Fig. 6 after barrel-polished;

30 Fig. 9 is a graph of the roughness curve of the surface of the aluminum nitride sintered body shown in Fig. 6 after lapped; and

Fig. 10 is a graph of the roughness curve of the surface of the aluminum nitride sintered body shown in Fig. 6 after polished through

multiple stages by a method according to the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

According to the present invention, the surface of a ceramic substrate is polished using the circumferential portion of a columnar- or disc-shaped, ductile rotating body containing abrasive grains. The rotating body has only to be able to hold abrasive grains and be ductile, and woven or nonwoven fabric, plastic foam (foamed plastic or sponge), rubber foam (rubber sponge) or the like is preferable. Such a material forming the rotating body is extremely easily deformed by pressure as compared to a conventional grinder or abrasive used in barrel-polishing.

The abrasive grains contained in the rotating body may be conventional abrasive grains such as alumina and silicon carbide.

Typically, there are recessed portions 10a and raised portions 10b as shown in Fig. 1 on the surface of a ceramic substrate formed of a sintered body, and the amplitude of the maximum irregularities is sometimes over 10 μ m. As an example of an aluminum nitride sintered body having such large irregularities on the surface, the surface roughness curve of a sintered body having a center line average height Ra of 0.78 μ m before polishing based on the Japanese Industrial Standard (JIS R 1600) and a maximum height Rmax of 9.7 μ m based on the standard is shown in Fig. 6.

By the polishing method according to the present invention, since the rotating body is ductile, the circumferential portion of the rotating body deforms toward the center when it is pressed against the ceramic surface. Thus, only raised portion 10b of recessed portion 10a and raised portion 10b shown in Fig. 1 is polished.

The resulting polished surface microscopically includes substantially flat portions 10c and recessed portions 10a remaining between flat portions 10c, so that a relatively smooth polished surface with a small irregularity amplitude can result for a smaller amount of polishing. Fig. 7 is a surface roughness curve resulting after polishing a aluminum nitride sintered body having a surface roughness shown in Fig. 6 using a rotating body containing abrasive grains of alumina (Al₂O₃)-based ceramic which passes a #320 mesh screen (hereinafter "#320 mesh-pass) by a method according to

the present invention. In Fig. 7, center line average height R_a is $0.34\mu\text{m}$ and maximum height R_{max} is $5.4\mu\text{m}$.

Note that "#320 mesh" refers to a mesh having 320 openings per linear inch. The size of the actual mesh is obtained by subtracting the
5 wire size forming the mesh from the value obtained by dividing one inch by 320. This also applies to #80 mesh, #150 mesh, #600 mesh, and #1000 mesh in the following description.

As compared to such polishing according to the present invention,
10 the conventional barrel-polishing mainly removes raised portions but removes recessed portions as well, and the raised and recessed portions are generally rounded off in polishing. Lapping, honing and grinding trim the entire surface regardless of the surface irregularities, and the resulting polished surface has impressions caused by hard abrasive grains or the like,
15 a large number of recessed and raised portions of a small amplitude remain microscopically.

The roughness curves of a barrel-polished product and a lapped product are given in Figs. 8 and 9 as examples of such a polished surface. The roughness curve in Fig. 8 corresponds to a surface resulting by barrel-polishing the surface of an aluminum nitride sintered body in Fig. 6 by a
20 #320-GC (Green Carbon) barrel stone, and the roughness curve in Fig. 9 corresponds to a surface resulting from lapping using a GC hone having a similar roughness.

As can be seen from comparison between the polished surface according to the present invention shown in Fig. 7 and the barrel-polished
25 surface in Fig. 8, although both are polished surfaces removed of raised portions of the original sintered body, they appear quite different. More specifically, the width of the flat portion of the polished surface (the width in the abscissa direction of the roughness curve) after the raised portion is removed is smaller than that by the barrel-polishing. The recessed portion
30 is shallow according to the barrel-polishing.

Furthermore, in the conventional barrel-polishing and lapping, a ceramic substrate is in point-contact with a hone or abrasive grains, a large pressure is locally applied upon the ceramic substrate. If the loaded

pressure is too large, the shoulder of a corner portion of the ceramic substrate is prone to be broken, rounded off, or chip. A relatively thin substrate could be cracked, in other words, the local concentration of pressure could damage the substrate. In a normal grinding, the substrate is ground as much as 0.1 to 0.2mm thickness-wise in order to avoid variations in grinding, a very large material loss is inevitable.

Meanwhile, the rotating body used according to the present invention is ductile and easily deforms when it is pressed against a ceramic substrate to be in plane-contact with the ceramic surface. As a result, the pressure upon the surface being polished is dispersed within each part of the ceramic substrate, which prevents the local concentration of pressure, and the ceramic substrate will be hardly damaged.

Therefore, by the polishing method according to the present invention, the pressure can be dispersed relatively evenly within a wide range of the surface being polished, a corner portion of the substrate will not be broken or rounded off, deformation such as cracks and chipping at the portion can be prevented and cracks in the substrate itself can be prevented so that the method is preferable for polishing a thin ceramic substrate, particularly a substrate having a thickness equal to or smaller than 2.0mm. In addition, the deformation of the rotating body and even distribution of abrasive grains reduce variations in the polishing and almost no material loss is caused.

By the polishing method according to the present invention, the polishing process is divided into a number of steps, and the average grain size of abrasive grains contained in the rotating body is reduced stepwise, and therefore the surface roughness of the resulting polished surface can be even further reduced. More specifically, the surface is polished first using a rotating body containing abrasive grains having a large average grain size. Since the average grain size is large, the polishing force is large accordingly, and large raised portions present on the surface are removed. Subsequently, rotating bodies each containing abrasive grains having an average grain size smaller than the previous polishing step are used for repeating the polishing.

For example, the grain size of abrasive grains contained in the rotating body is set as #80 mesh-pass first, then #150 mesh-pass next, followed by #320 mesh-pass sequentially, so that small raised portions which cannot be removed in a polishing step can be removed in the following steps.

Fig. 10 shows the roughness curve of a surface formed by polishing the surface of an aluminum nitride sintered body having the surface state shown in Fig. 6 in the multiple steps, and center line average height R_a is $0.16\mu\text{m}$ and R_{max} is $1.5\mu\text{m}$. By such multi-step polishing, the surface to be polished can be prevented from being damaged using the ductile rotating body, while the surface roughness of the polished surface can be more reduced.

In a polishing operation, a ceramic substrate is moved while the surface is contacted to the body rotating. At this time, as shown in Fig. 3 polishing is preferably performed such that the direction (rotating direction) D_1 orthogonal to the rotating axis of rotating body 11 is inclined relative to the polishing direction D_0 of ceramic substrate 10. If polishing direction D_0 and rotating direction D_1 are the same, impressions caused by abrasive grains are formed linearly on ceramic substrate 10, the surface roughness is relatively increased. Meanwhile, if prescribed angle θ is formed between polishing direction D_0 and rotating direction D_1 , linear impressions will not be formed, and a smoother polished surface results. Angle θ is preferably in the range from 10° to 80° and more preferably in the range from 30° to 60° .

The polished surface of a ceramic substrate obtained by the above described polishing method according to the present invention includes flat portions and recessed portions therebetween. The flat portions have an average width in the range from several μm to $50\mu\text{m}$ microscopically, and preferably includes ups and downs (fine irregularities) equal to or smaller than $0.2\mu\text{m}$ raised toward the surface.

The ceramic substrate to be polished is not particularly limited and may be an alumina, aluminum nitride, silicon nitride substrate or the like. Since the aluminum nitride substrate is generally formed by grains as

large as several μm , grains often drop out by stress applied in a polishing operation, and this is why it is difficult to obtain a smooth surface by a conventional method, but the pressure against the surface being polished is dispersed according to the present invention, which prevents the drop out
5 of grains caused by the concentration of the pressure, so that an even smoother polished surface results.

The polished surface formed by the polishing method according to the present invention includes substantially flat portions and recessed portions therebetween, the height of microscopical raised portions on the
10 flat portions is small, a relatively smooth surface with a small irregularity amplitude results, and therefore when the surface is used as a sliding surface sliding on another material and/or object, a preferable sliding characteristic results. Furthermore, by positioning the ceramic substrate such that the rotation or moving direction of a workpiece is aligned or
15 approximated to the (constant) rotation direction of the rotating body in a polishing operation, the friction resistance with the workpiece can be reduced, which allows for a higher sliding characteristic.

The sliding characteristic of a ceramic substrate according to the present invention is particularly advantageous when a workpiece to slide
20 on is softer than the ceramic substrate, because the substantially flat portions having a small raised portion are in contact with the workpiece while sliding so that the friction resistance is small and the attacking force on the workpiece is small. For example, since a ceramic heater used in a thermal fixation device for toner image slides on a heat-resisting resin film,
25 the ceramic substrate according to the present invention is particularly advantageously used for the substrate for the ceramic heater. Meanwhile, the recessed portion of the polished surface is preferably reduced as much as possible in order to improve the sliding characteristic. To this end, however, time required for polishing is prolonged, which impedes the
30 productivity and therefore the time required for polishing must be set not to impede the productivity.

Note that in a thermal fixation device for toner image, as shown in Fig. 4, a resin support body 2 is attached with a ceramic heater 1, a heat-

resisting resin film 3 is rotatably provided at the outer circumferential portion of support body 2, and a pressurizing roller 4 is disposed opposite to ceramic heater 1 with heat-resisting resin film 3 therebetween. A transfer material 5 having an unfixed toner image 6a is transferred at a prescribed speed between pressurizing roller 4 and heat-resisting resin film 3, pressurized by pressurizing roller 4 and heated by ceramic heater 1, so that toner image 6b is fixed on transfer material 5.

First Embodiment

Ceramic powder materials Al_2O_3 , AlN and Si_3N_4 were each added with a sintering aid, then an organic solvent and a binder, and mixed by a ball mill to obtain their slurries. The resultant slurries were each formed into a sheet by a doctor blade method and cut into a prescribed shape, followed by degreasing in a nitrogen atmosphere at 900°C . Then, these ceramic materials were sintered in a non-oxidizing atmosphere at optimum temperatures for them and formed into ceramic substrates.

More specifically, 5.0 % by weight of CaO , SiO_2 , and MgO were added as sintering aids to the Al_2O_3 material powder, and the compact thereof was sintered in air at 1800°C and formed into an Al_2O_3 substrate. Three % Y_2O_3 by weight is added as a sintering aid to the AlN material powder, and the compact thereof was sintered in nitrogen at 1820°C and formed into an AlN substrate. Five % Y_2O_3 by weight and 2.0 % Al_2O_3 by weight were added as sintering aids to the Si_3N_4 , and the compact was sintered in nitrogen at 1700°C and then subjected to HIP (Hot Isostatic Pressing) under 100MPa at 1800°C to obtain a Si_3N_4 substrate.

As samples of each of the ceramics thus obtained, those having different substrate sizes (length $\times$ width $\times$ thickness (mm)) and different center line average heights R_a (μm) as surface roughnesses before polishing as given in Table 1 below were prepared. The three-point bending strengths of prepared samples 1 to 6, Al_2O_3 substrates, samples 7 to 12, AlN substrates, and samples 13 to 18, Si_3N_4 substrates were 350Mpa, 350Mpa, and 900Mpa, respectively.

Table 1

Sample	Ceramic	Substrate size (mm)	Surface roughness Ra (μm)
1	Al_2O_3	$30 \times 30 \times 0.5$	0.42
2	Al_2O_3	$30 \times 30 \times 0.3$	0.42
3	Al_2O_3	$100 \times 100 \times 0.5$	0.42
4	Al_2O_3	$100 \times 100 \times 0.3$	0.42
5	Al_2O_3	$300 \times 100 \times 2.0$	0.42
6	Al_2O_3	$300 \times 100 \times 2.5$	0.42
7	AlN	$30 \times 30 \times 0.5$	0.85
8	AlN	$30 \times 30 \times 0.3$	0.86
9	AlN	$100 \times 100 \times 0.5$	0.79
10	AlN	$100 \times 100 \times 0.3$	0.90
11	AlN	$300 \times 100 \times 2.0$	0.83
12	AlN	$300 \times 100 \times 2.5$	0.88
13	Si_3N_4	$30 \times 30 \times 0.5$	0.75
14	Si_3N_4	$30 \times 30 \times 0.3$	0.64
15	Si_3N_4	$100 \times 100 \times 0.5$	0.66
16	Si_3N_4	$100 \times 100 \times 0.3$	0.66
17	Si_3N_4	$300 \times 100 \times 2.0$	0.69
18	Si_3N_4	$300 \times 100 \times 2.5$	0.70

Using each of the samples in Table 1, normal vibration barrel-polishing, lapping and polishing according to the present invention were performed. In the barrel-polishing, an alumina ball abrasive having a diameter of 5.0mm and a vibrating barrel device having a container diameter of 1m were used and the vibration was at 60Hz. In the lapping, a #600 diamond abrasive was used. In the polishing according to the present invention, #150 mesh-pass alumina abrasive grains were contained in a rotating body of nylon nonwoven fabric having a diameter of 300mm, and the rotating body was used to perform dry polishing at a rotating speed of 1000 rev/min. A reduction in the thickness of the ceramic substrate after the polishing was intended to be not more than 0.02mm, and the thickness given in Table 1 was set as a target.

For the thickness of the ceramic substrate obtained by each of the above polishing, center line average height Ra (μm) as a surface roughness after the polishing and a material loss (% by weight) by the polishing were measured, and the result is given in the following Table 2. Each of Si_3N_4

substrate samples has a bending strength greater than Al_2O_3 and AlN substrate samples, damages to the samples were relatively small by any of the polishing methods.

5

Table 2

Sample	Lapping		Barrel-polishing		Present invention	
	Ra after polishing (μm)	Material loss (wt%)	Ra after polishing (μm)	Material loss (wt%)	Ra after polishing (μm)	Material loss (wt%)
1	0.31	41	0.25	0.3	0.32	0.1
2	Substrate crack	-	Edge chip	0.5	0.30	0.1
3	0.31	40	Substrate crack	-	0.31	0.1
4	Substrate crack	-	Substrate crack	-	0.31	0.1
5	0.33	21	Substrate crack	-	0.29	0.1
6	0.32	17	0.28	0.3	0.27	0.1
7	0.39	42	0.28	0.3	0.29	0.1
8	Substrate crack	-	Edge chip	0.4	0.31	0.1
9	0.36	39	Substrate crack	-	0.29	0.1
10	Substrate crack	-	Substrate crack	-	0.30	0.1
11	0.40	20	Substrate crack	-	0.23	0.1
12	0.39	17	0.26	0.2	0.24	0.1
13	0.37	40	0.27	0.2	0.31	<0.1
14	0.35	35	0.26	0.2	0.32	<0.1
15	0.38	39	0.27	0.2	0.31	<0.1
16	Substrate crack	-	Substrate crack	-	0.30	<0.1
17	0.34	22	Edge chip	-	0.28	<0.1
18	0.35	18	0.24	0.2	0.27	<0.1

Based on the above result, by the barrel-polishing and lapping, cracks were generated in a thin and large substrate, while by the polishing according to the present invention, deformation at a corner portion,

rounding, and chipping, not to mention cracks in the substrates were not caused, and still a better surface roughness resulted, particularly for a silicon nitride substrate as compared to the other polishing methods.

5 When the material loss in the substrate is compared, reduction in the thickness of the ceramic substrate according to the present invention is from 4 μ m to 6 μ m at most, in other words, there was little material loss, while the material loss was great according to the conventional methods, particularly according to the lapping.

Second Embodiment

10 Using sample 10, an AlN substrate according to the first embodiment, improvements in the surface roughness by multi-step polishing were observed. More specifically, in each of the steps, alumina abrasive grains were contained in a rotating body of nylon nonwoven fabric having a diameter of 300mm, and polishing was performed at a rotating speed of
15 1000 rev/min. In the multi-step polishing, a rotating body containing #150 mesh-pass was used first, then the grain size of abrasive grains was reduced stepwise to #320 mesh-pass, then to #600 mesh-pass and then to #1000 mesh-pass. Center line average height Ra was measured as the surface roughness of a substrate obtained in each step, and the result is
20 given in the following Table 3.

For the purpose of comparison, the same sample 10, an AlN substrate was polished by rotating bodies containing #320 mesh-pass, #600 mesh-pass and #1000 mesh-pass alumina grains, and then again polished using rotating bodies containing alumina grains of larger sizes, in other
25 words, 150# mesh-pass, #320 mesh-pass and #600 mesh-pass alumina abrasive grains. The center line average height Ra of each of the resulting substrates was measured as the surface roughness, and the result is given as the surface roughness Ra after the polishing in the following Table 3.

Table 3

Abrasive grain size	Surface roughness before polishing Ra(μm)	Surface roughness after polishing Ra(μm)	Surface roughness after re-polishing Ra(μm)
#150	0.90	0.30	-
#320	0.30	0.21	0.28
#600	0.21	0.15	0.20
#1000	0.15	0.12	0.15

As can be seen from the result, in the multi-step polishing, a rotating body containing abrasive grains smaller stepwise than that in the previous stage is used for polishing, so that the surface roughness of the polished surface can be further improved.

Third Embodiment

Using sample 10, an AlN substrate according to the first embodiment, polishing was performed at different angles θ between the advancing direction of the AlN substrate (the polishing direction) and the rotating direction of the rotating body, and the influence of angle θ upon the surface roughness of the resulting polished surface was observed. The polishing conditions were the same as those of the first embodiment except that the rotating body used contained #150 mesh-pass alumina abrasive grains.

Table 4

Angle θ ($^{\circ}$)	Surface roughness before polishing Ra (μm)	Surface roughness after polishing Ra (μm)
0	0.90	0.30
5	0.90	0.29
10	0.90	0.24
30	0.90	0.18
45	0.90	0.16
60	0.90	0.17
80	0.90	0.25
90	0.90	0.32

As in the above Table 4, changing angle θ formed between the rotating direction of the rotating body and the polishing direction of the

substrate changes the surface roughness, and the surface roughness Ra of the AlN substrate after polishing is significantly reduced when angle θ is in the range from 10° to 80° , more preferably in the range from 30° to 60° than when the angle is 0° (in parallel) and 90° (at right angles).

5 Fourth Embodiment

Similarly to the first embodiment, an AlN substrate having a length of 300mm, a width of 10mm and a thickness of 1.0mm and an AlN substrate having a length of 100mm, a width of 300mm and a thickness of 1.3mm were manufactured. The following polishing operations were
10 performed to these AlN substrates.

The AlN substrate as thick as 1.0mm was wet-polished using a nylon sponge rotating body containing SiC abrasive grains having a diameter of 400mm at a rotating speed of 800 rev/min while applying water to the rotating body. More specifically, angle θ formed between the rotating
15 direction and the polishing direction was 30° , and the grain size of abrasive grains was changed from #150 mesh-pass, to #320, #600 and to #1000 mesh-pass stepwise for multi-step polishing.

Meanwhile, the AlN substrate as thick as 1.3mm was polished to 1.0mm by lapping and cut into a piece of 300mm $\times$ 10mm.

Each of the AlN substrates after polishing was used to manufacture a ceramic heater 1 used in a thermal fixation device for toner image as shown in Fig. 5. More specifically, a heating element 1b was formed by Ag-Pd paste by screen printing and an electrode 1d was formed by Ag paste at the polishing surface of each ceramic substrate 1a, followed by baking in
20 atmosphere at 880°C . Then, glass paste was applied onto heating element 1b by screen printing, followed by baking at 700°C in atmosphere to form a protection film 1c.

Ceramic heaters 1 thus obtained were each attached to a thermal fixation device for toner image as shown in Fig. 4 and its durability was
30 tested. In the durability testing, the temperature of ceramic heater 1c was set to 180°C , and the rotation number of pressurizing roller 4 and heat-resisting resin film 3 was set to 40 rev/min.

As a result, in the ceramic heater using the AlN substrate polished

according to the present invention, there was no departed grains between the heat-resisting resin film and the heater after 1000 hours, good sliding characteristic was secured, and no change was observed in the rotating speed of the heat-resisting film from the speed at the start of the durability test.

5 Meanwhile, in the ceramic heater using the lapped AlN substrate, the heat-resisting resin film stopped rotating after 150 hours since the start of the durability test. Observing the sliding surface between the heat-resisting resin film and the heater revealed that departed AlN grains were present which probably impaired the sliding ability and stopped the rotation of the heat-resisting film.

10 As in the foregoing, according to the present invention, a ceramic substrate having a small thickness and a large area can be easily and inexpensively polished without damages such as cracks to produce a polished surface having high smoothness. The invention is particularly suitable for polishing an aluminum nitride substrate, grains of which easily depart. An aluminum nitride substrate polished according to the present invention is particularly preferably used as a substrate for a ceramic heater in a thermal fixation device for toner image.

20 Although the present invention has been described and illustrated in detail, it is clearly understood that the same is by way of illustration and example only and is not to be taken by way of limitation, the spirit and scope of the present invention being limited only by the terms of the appended claims.

THE EMBODIMENTS OF THE INVENTION IN WHICH AN EXCLUSIVE PROPERTY OR PRIVILEGE IS CLAIMED ARE DEFINED AS FOLLOWS:

1. A method of polishing a ceramic substrate, wherein
a ductile rotating body containing abrasive grains is used, and one surface of the ceramic substrate is polished while the ceramic substrate is moved in one direction, wherein a thickness of the ceramic substrate is, at most, 2.0 mm; and
a direction orthogonal to the rotating axis of the rotating body is inclined at an angle in the range of from 10° to 80° relative to a polishing direction of the ceramic substrate being polished.
2. A method according to claim 1, wherein
the polishing of the ceramic substrate is divided into two or more steps, and the grain size of abrasive grains contained in the rotating body is reduced stepwise for polishing.
3. A method of polishing a ceramic substrate, comprising:
providing and rotating a first ductile body containing first abrasive grains;
polishing a first surface of the ceramic substrate using the rotating first ductile body, by contacting a circumferential portion of the rotating first ductile body onto the first surface of the ceramic substrate; and
linearly moving one of the first ductile body and the ceramic substrate or both thereof relative to each other along a linear polishing direction while carrying out the polishing, wherein the linear polishing direction is oriented at

an angle in a range from 10° to 80° relative to a rotation direction that is orthogonal to a rotation axis about which the first ductile body is rotating.

4. A method according to claim 3, additionally comprising:
providing and rotating a second ductile body containing second abrasive grains having a smaller grain size than the first abrasive grains of the first ductile body; and
further polishing the first surface of the ceramic substrate using the rotating second ductile body after the polishing using the rotating first ductile body, by contacting a circumferential portion of the rotating second ductile body onto the first surface of the ceramic substrate.
5. A method according to claim 3 or 4, wherein the ceramic substrate has a thickness of at most 2.0 mm.

FIG. 1

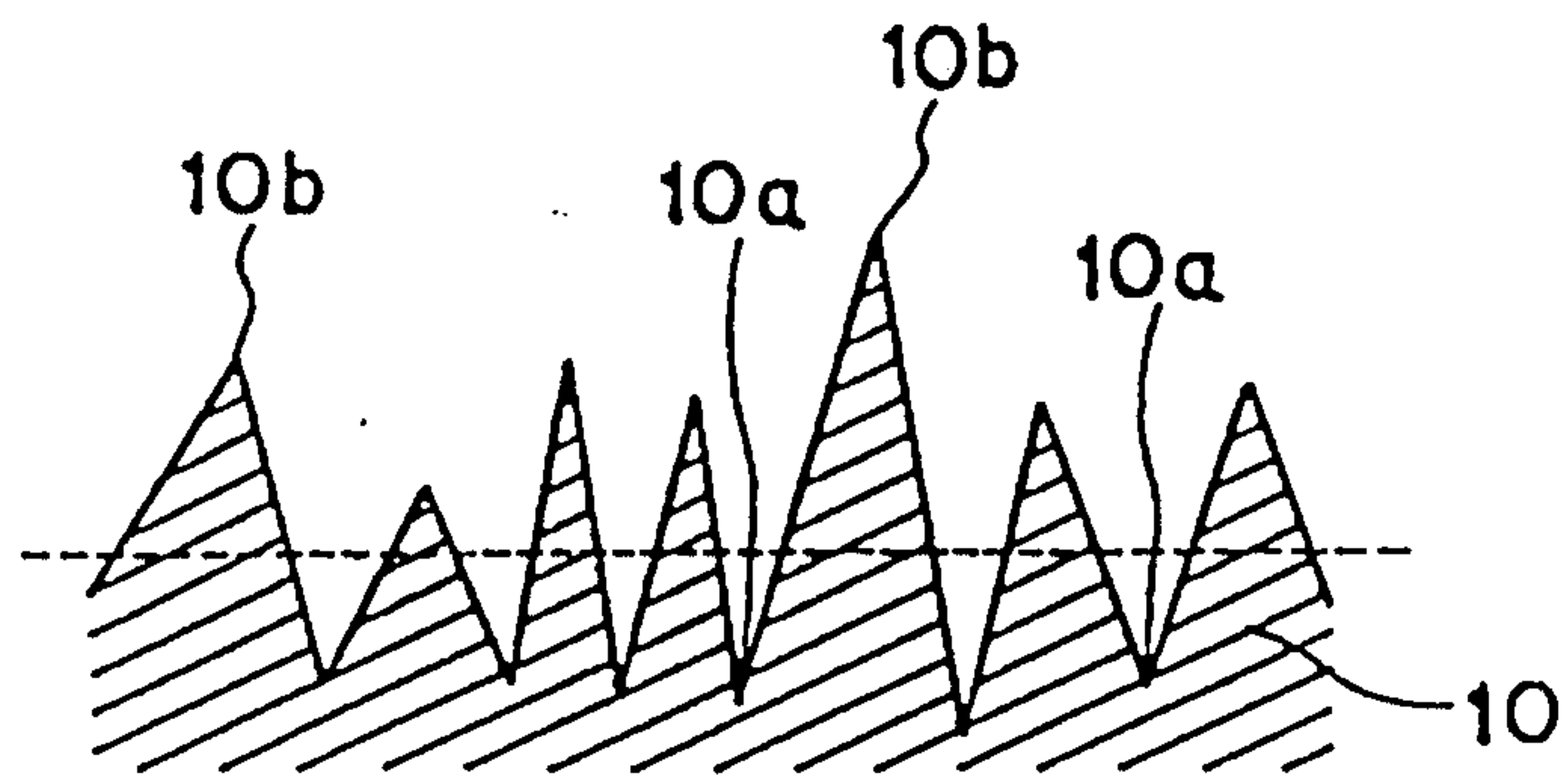


FIG. 2

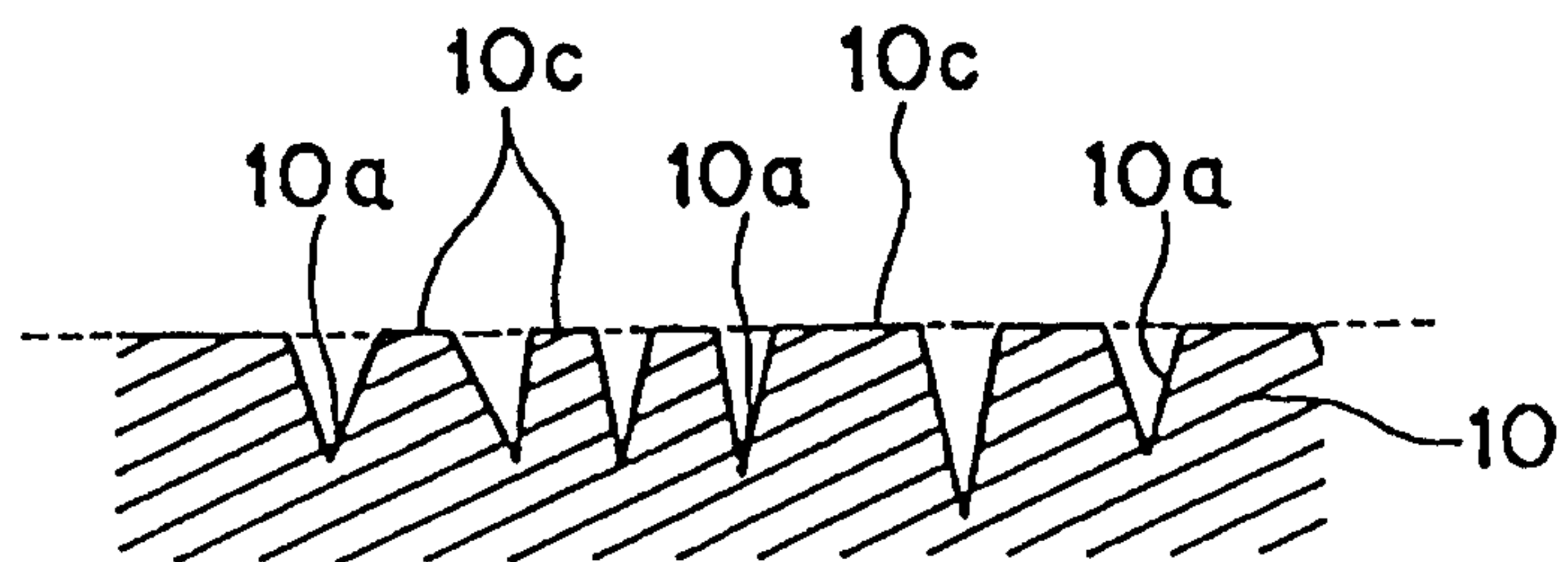


FIG. 3

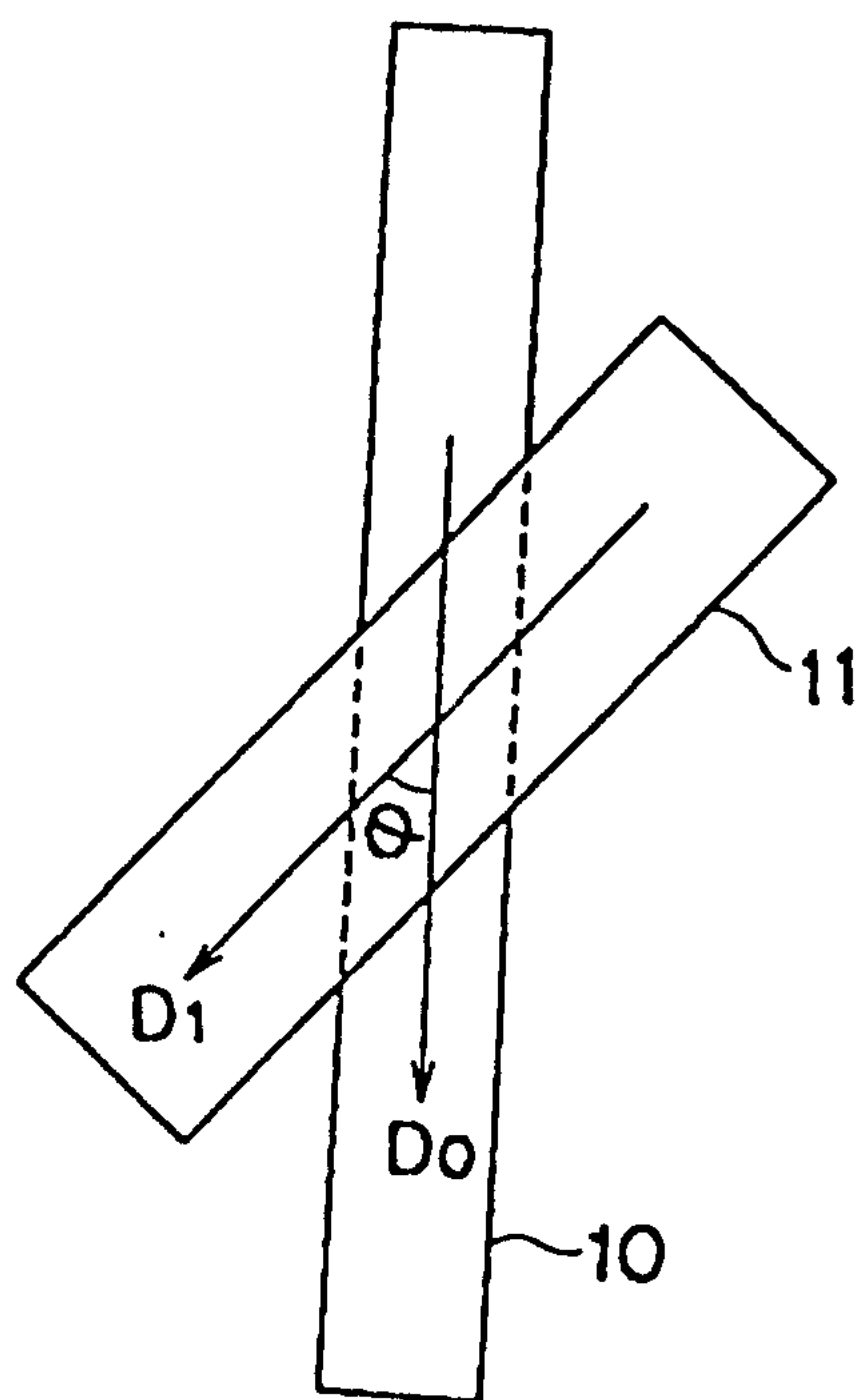


FIG. 4

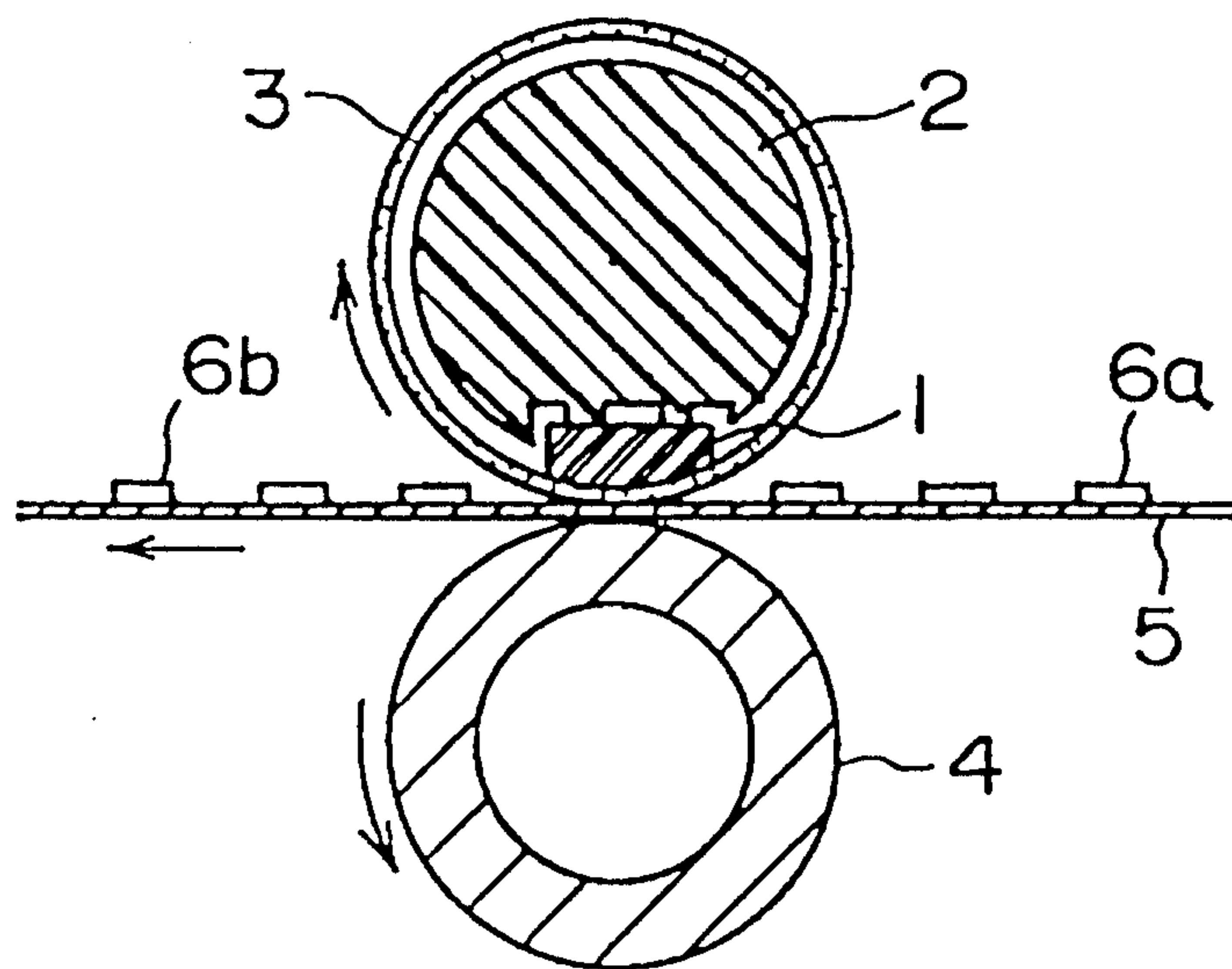


FIG. 5

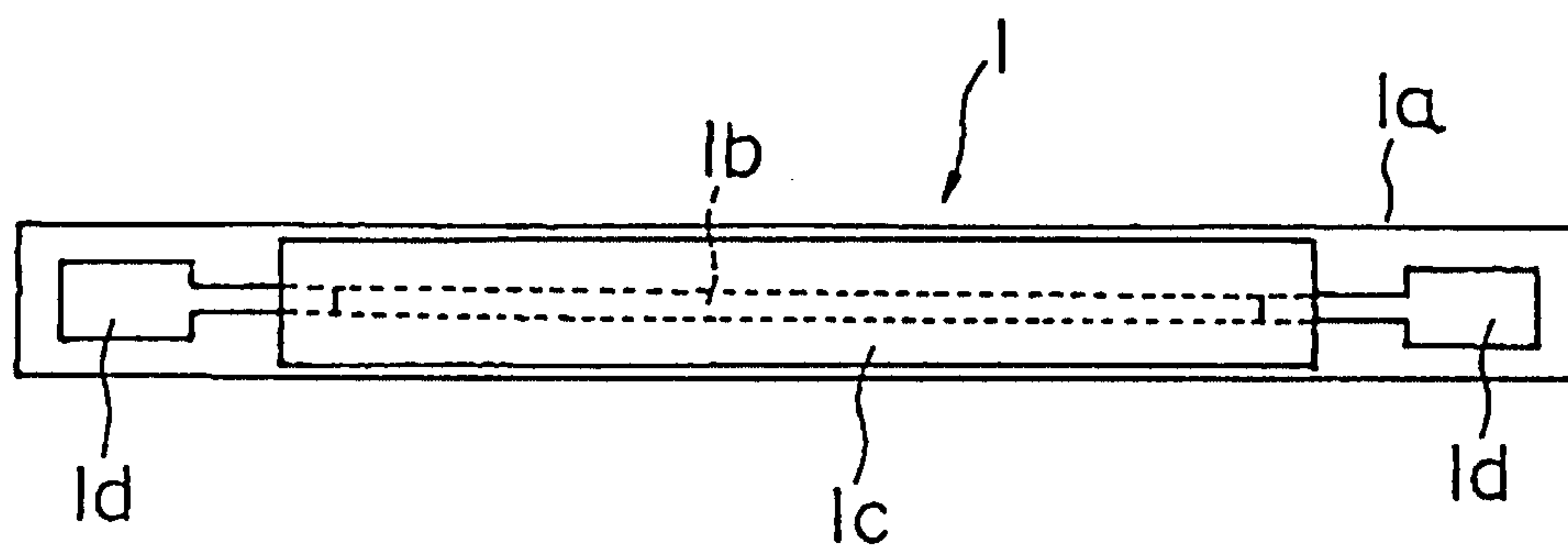


FIG. 6

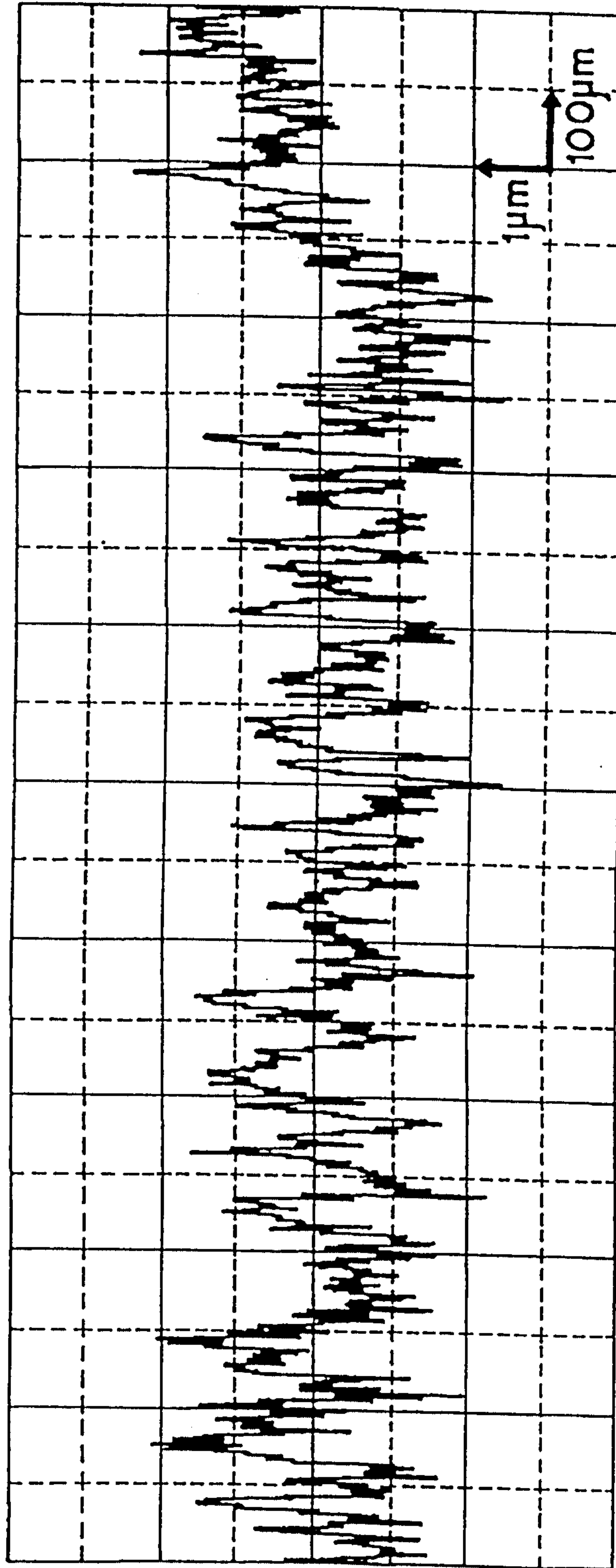


FIG. 7

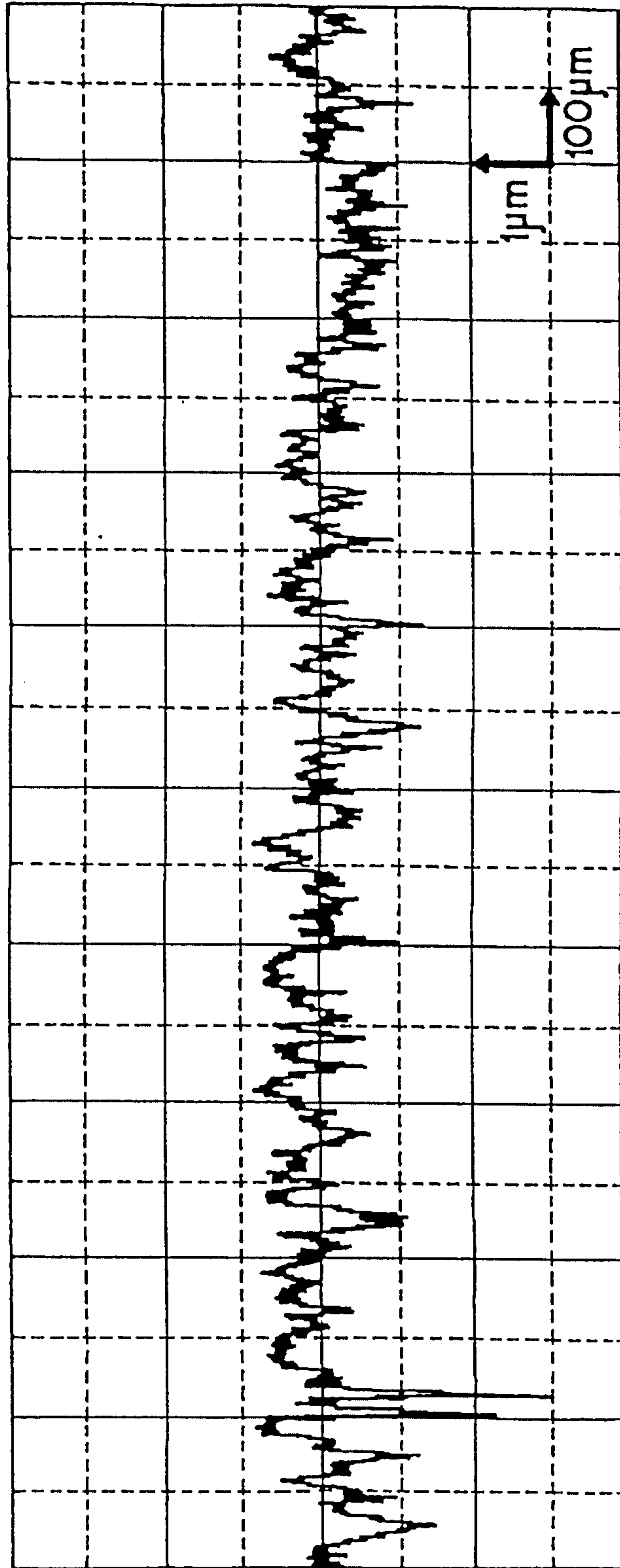


FIG. 8

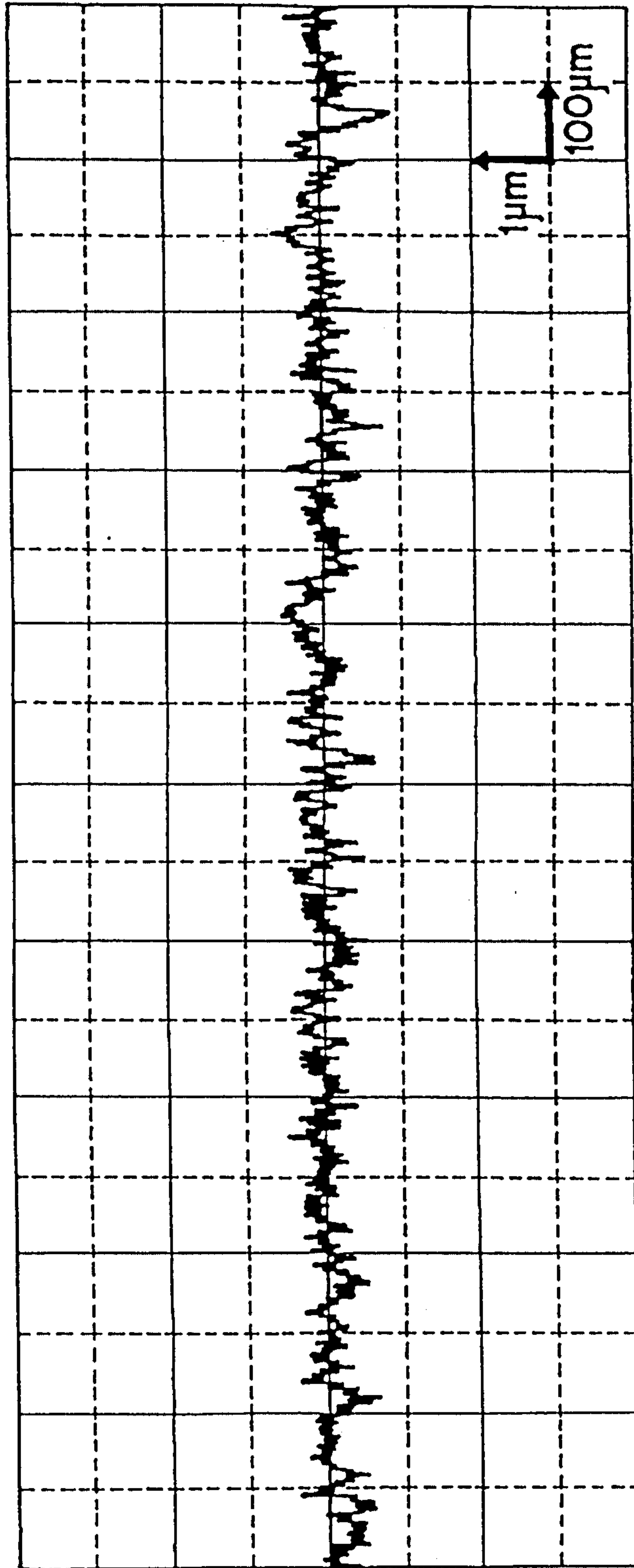


FIG. 9

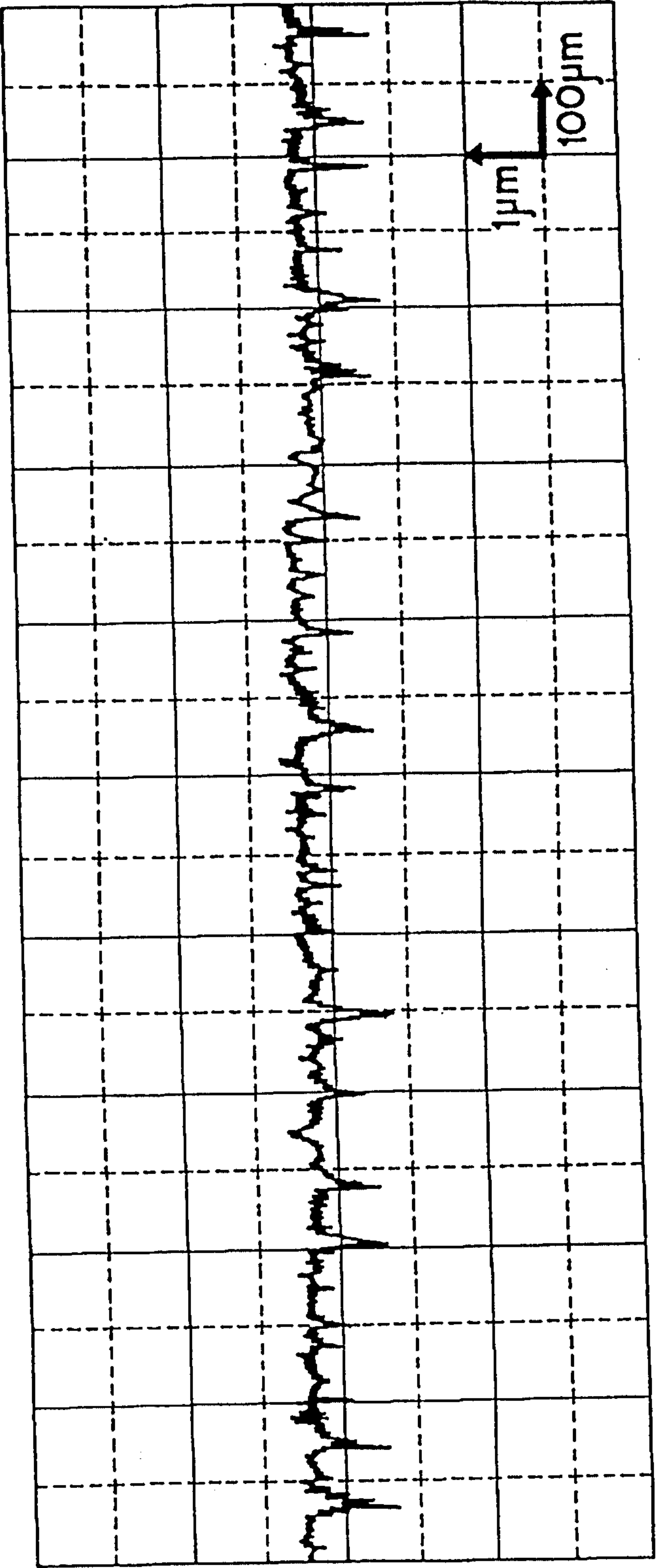


FIG. 10

